

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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CEDM7001

SURFACE MOUNT SILICON N-CHANNEL ENHANCEMENT-MODE MOSFET



SOT-883L CASE

APPLICATIONS:

- Load/Power switches
- DC DC converters
- Battery powered portable equipment

Central
Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CEDM7001 is an N-Channel Enhancement-mode silicon MOSFET, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers low $r_{\mbox{\footnotesize{DS}}(\mbox{\footnotesize{ON}})}$ and low the shold voltage.

MARKING CODE: H

COMPLEMENTARY P-CHANNEL: CEDM8001

FEATURES:

- 100mW Power Dissipation
- 0.4mm low package profile
- Low rDS(ON)
- Low threshold voltage
- · Logic level compatible
- Small leadless surface mount package

MAXIMUM RATINGS : $(T_A=25^{\circ}C)$	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	10	V
Continuous Drain Current (Steady State)	I_{D}	100	mA
Peak Drain Current, tp=10µs	I_{DM}	200	mA
Power Dissipation	P_{D}	100	mW
Operating and Storage Junction Temperature	$T_{\rm J}, T_{\rm sta}$	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
IGSSF, IGSSR	V_{GS} =10V, V_{DS} =0			1.0	μΑ
IDSS	V_{DS} =20V, V_{GS} =0			1.0	μΑ
BV _{DSS}	$V_{GS}=0, I_{D}=100\mu A$	20			V
V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.6		0.9	V
rDS(ON)	V_{GS} =4.0V, I_D =10mA		0.9	3.0	Ω
rDS(ON)	V_{GS} =2.5V, I_D =10mA		1.3	4.0	Ω
rDS(ON)	V _{GS} =1.5V, I _D =1.0mA			15	Ω
9FS	V _{DS} =10V, I _D =100mA	100			mS
C _{rss}	V_{DS} =3.0V, V_{GS} =0, f=1.0MHz		4.0		pF
C _{iss}	V_{DS} =3.0V, V_{GS} =0, f=1.0MHz		9.0		pF
Coss	V_{DS} =3.0V, V_{GS} =0, f=1.0MHz		9.5		pF
Q _{g(tot)}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =100mA		0.566		nC
Q _{gs}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =100mA		0.16		nC
Q_{gd}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =100mA		0.08		nC
ton	V_{DD} =3.0V, V_{GS} =2.5V, I_{D} =10mA		50		ns
t _{off}	V_{DD} =3.0V, V_{GS} =2.5V, I_{D} =10mA		75		ns

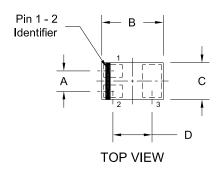
R9 (19-September 2014)

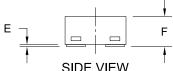
CEDM7001

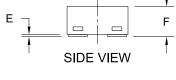
SURFACE MOUNT SILICON N-CHANNEL ENHANCEMENT-MODE MOSFET

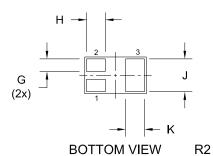


SOT-883L CASE - MECHANICAL OUTLINE









DIMENSIONS				
	INCHES		MILLIM	ETERS
SYMBOL	MIN	MAX	MIN	MAX
Α	0.014		0.	35
В	0.037	0.041	0.95	1.05
С	0.022	0.026	0.55	0.65
D	0.026		0.65	
Е	0.000	0.002	0.00	0.05
F	0.012	0.016	0.30	0.40
G	0.005	0.007	0.13	0.18
Н	0.008	0.012	0.20	0.30
J	0.018	0.022	0.45	0.55
K	0.008	0.012	0.20	0.30
COT 9931 (DEV/-D2)				

SOT-883L (REV:R2)

LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: H

Package Type Options (all dimensions are maximum - in mm)

Package	Length	Width	Height	P _D (mW)	Central Item Number
SOT-883L	1.05	0.65	0.40	100	CEDM7001
SOT-883VL	1.05	0.65	0.32	100	CEDM7001VL
SOT-953	1.05	1.05	0.50	250	CMNDM7001
SOT-523	1.70	1.70	0.78	250	CMUDM7001

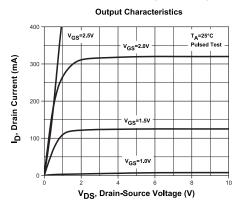
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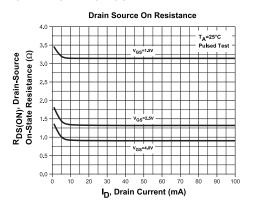
CEDM7001

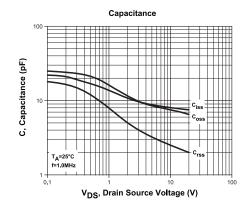
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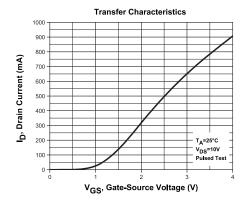


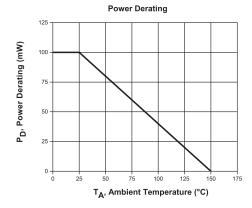
TYPICAL ELECTRICAL CHARACTERISTICS











R9 (19-September 2014)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- · Special wafer diffusions
- PbSn plating options
- · Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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